

Title (en)

METHOD OF ENHANCING THE STRENGTH OF SEMICONDUCTOR WAFERS OR CHIPS

Title (de)

VERFAHREN ZUR VERSTÄRKUNG VON HALBLEITERWAFERN ODER CHIPS

Title (fr)

PROCÉDÉ POUR OPTIMISER LA RÉSISTANCE DE TRANCHES OU DE PUCES SEMI-CONDUCTRICES

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Application

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Abstract (en)

[origin: WO2010083995A2] The present invention relates to a method of enhancing the strength of a semiconductor wafer or semiconductor chip, the semiconductor wafers being sliced from an ingot or cut from a foil and preprocessed in one or several preprocessing steps prior to further processing steps for generating semiconductor elements. In the proposed method at least one annealing step is performed in addition to the one or several preprocessing steps and processing steps. With the proposed method the fracture strength of semiconductor wafers can be significantly enhanced thus allowing the use of semiconductor wafers with a higher degree of damages and increasing the yield of the whole wafer processing.

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